

SANYO Semiconductors DATA SHEET

LV0223CV — For Optical Pickups Front Monitor OE-IC

Overview

The LV0223CV is a front monitor optoelectronic IC for optical pickups that has a built-in photo diode compatible with three waveforms. LV0223CV is small size and type CSP packages.

Functions

- PIN photodiode compatible with three wavelengths incorporated.
- Gain adjustment (-6dB to +6dB in 256 steps) through serial communication.
- Amplifier to amplify differential output.

Specifications

Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{CC}		6	V
Allowable power dissipation	Pd	Glass epoxy both-side substrate 55mm × 45mm × 1.6mm Copper foil area (head: about 90% Tail: about 90%), Ta=75°C	143	mW
Operating temperature	Topr		-20 to +75	°C
Storage temperature	Tstg		-40 to +100	°C

Recommended Operating Conditions at Ta = 25°C

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Parameter	Symbol Conditions		min	typ	max	Unit	
Operating supply voltage	VCC		4.5	5	5.5	V	
Output load capacitance	CO		12	20	33	pF	
Output load resistance	z _O		3			kΩ	

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LV0223CV

Electrical Characteristics at $Ta = 25^{\circ}C$, $V_{CC} = 5V$, $RL=6k\Omega$, CL=20pF

D		Conditions		Ratings		
Parameter	Symbol	Conditions	min	typ	max	Unit
Current dissipation	Icc		13.3	17	22.1	mA
Sleep current	Islp				0.6	mA
Output voltage when shielded	VС	At shielding	1.85	2.0	2.15	V
Output offset voltage	Vofs	At shielding, voltage between VOP-VON	-30	0	30	mV
Temperature dependence of offset voltage *1	Vofs	Ta=-10 to +75°C	-60	0	60	μV/°C
Optical output voltage *1	VLC	Low Gain, λ=780nm, G=0dB	0.21	0.262	0.31	mV/μW
Voltage between VOP-VON	VLD	Low Gain, λ=650nm, G=0dB	0.22	0.275	0.33	mV/μW
	VLB	Low Gain, λ=405nm, G=0dB	0.14	0.172	0.21	mV/μW
	VM1C	Middle1 Gain, λ=780nm, G=0dB	0.66	0.83	0.99	mV/μW
	VM1D	Middle1 Gain, λ=650nm, G=0dB	0.70	0.87	1.05	mV/μW
	VM1B	Middle1 Gain, λ=405nm, G=0dB	0.43	0.54	0.65	mV/μW
	VM2C	Middle2 Gain, λ=780nm, G=0dB	1.97	2.46	2.95	mV/μW
	VM2D	Middle2 Gain, λ=650nm, G=0dB	2.07	2.58	3.10	mV/μW
	VM2B	Middle2 Gain, λ=405nm, G=0dB	1.29	1.62	1.94	mV/μW
	VH1C	High1 Gain, λ=780nm, G=0dB	3.35	4.19	5.02	mV/μW
	VH1D	High1 Gain, λ=650nm, G=0dB	3.52	4.40	5.28	mV/μW
	VH1B	High1 Gain, λ=405nm, G=0dB	2.20	2.75	3.30	mV/μW
	VH2C	High2 Gain, λ=780nm, G=0dB	5.72	7.15	8.58	mV/μW
	VH2D	High2 Gain, λ=650nm, G=0dB	6.02	7.52	9.02	mV/μW
	VH2B	High2 Gain, λ=405nm, G=0dB	3.76	4.70	5.64	mV/μW
Light output voltage adjustment range *1	G	G=0dB reference, absolute value of adjustment width	5.5	6.0	6.5	dB
D range *1	VoD	Voltage between VOP-VON	1700	2200		mV
Frequency characteristics *1, *2	FcC	-3dB(1MHz reference), λ=780nm	60	80		MHz
		Light input = 40μ W(DC) + 20μ W(AC)				
	FcD1	-3dB(1MHz reference), λ=650nm	60	85		MHz
		Light input = 40μ W(DC) + 20μ W(AC)				
	F-D0	Low/Middle1/2 Gain		00		NAL I-
	FcD2	-3dB(1MHz reference), λ=650nm Light input = 40μW(DC) + 20μW(AC)	60	80		MHz
		High1/2 Gain				
	FcB1	-3dB(1MHz reference), λ=405nm	60	85		MHz
		Light input = 40μ W(DC) + 20μ W(AC)				
		Low/Middle1/2 Gain				
	FcB2	-3dB(1MHz reference), λ=405nm	60	80		MHz
		Light input = 40μW(DC) + 20μW(AC) High1/2 Gain				
Settling time *1	Tset	riigiri/2 Gairi		10	15	ns
Response time *1	Tr, Tf	Vo=0.9Vp-p, output level 10 to 90%		4	10	ns
	,	fc=10MHz, duty=50%				
Overshoot *1	Ovst	Vo=0.9Vp-p, G=0dB			15	%
Undershoot *1	Unst	Vo=0.9Vp-p, G=0dB			15	%
Linearity *1	Lin	At output voltage 0.5V and 1.0V	-1	0	1	%
Light-output voltage temperature dependence	TC	(Between VOP-VON) λ=780nm, 25°C reference	7	10	12	%
Voltage between VOP-VON *1, *3	TD	λ=780nm, 25 C reference λ=650nm, 25°C reference	-1	2	13 5	%
· · · · · ·	TB	·				
tem with *1 mark indicate the decign reference va		λ=405nm, 25°C reference	-1	2	5	%

Item with *1 mark indicate the design reference value.

Item with *2 mark indicate the frequency characteristics when VOP and VON are applied individually.

The frequency characteristics are for the output voltage adjustment range is -6 to +6dB $\,$

Item with *3 mark indicates the temperature dependence for the case of High2 / High1 / Middle2 / Middle1 / Low gain and for the case when the temperature is 25 to 75°C for the output voltage adjustment range of -6 to +6dB

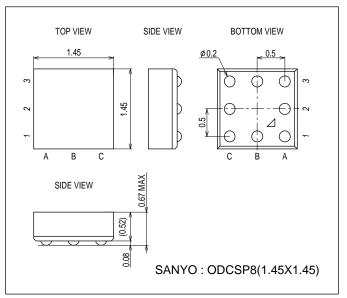
[Expression of output voltage]

 V_{N} = (sensitivity / 2) \times 5400 / (5400-16 \times GCAstep) \times light intensity (µW)

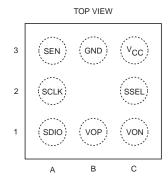
Package Dimensions

unit: mm (typ)

3407

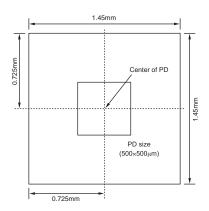


Pin Assignment



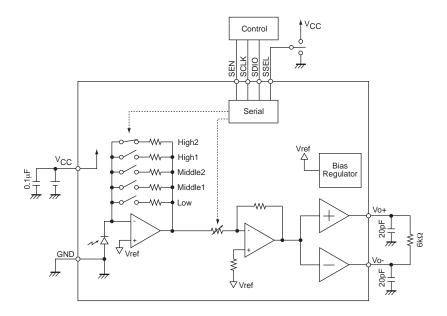
		•
Pin No.	Pin name	Function
1A	SDIO	Serial communication Data pin
1B	VOP	Positive side output pin
1C	VON	Negative side output pin
2A	SCLK	Serial communication Clock pin
2C	SSEL	Register selection pin
		SSEL = Low: Address 00 to 0Fh used
		SSEL = High : Address 10 to 1Fh used
		SSEL = Open : Address 70 to 7Fh used
3A	SEN	Serial communication Enable pin
3B	GND	GND pin
3C	Vcc	Power supply voltage pin

PD assignment



^{*}PD size for reference to be used for design

Block diagram and Test circuit diagram



Resister table

Enable selection of the register group from the SSEL pin.

SSEL = Low

	Address	7	6	5	4	3	2	1	0
Name		РО	WER	IV GA	IV GAIN SEL		N SEL	IV GAIN2	
Default	1	(00		00	(00	1	0
Value	00h	11: Po	ower on		*4	00/0	1: BD	*4	
		00/01/1	0: Sleep			10:	DVD		
						11:	CD		
Name]				BD (GAIN			
Default	01h	1	1	1	1	1	1	1	1
Value			00000000 to 11111111						
Name					DVD	GAIN			
Default	02h	1	1	1	1	1	1	1	1
Value					00000000 t	to 11111111			
Name]				CD	GAIN			
Default	03h	1	1	1	1	1	1	1	1
Value		00000000 to 11111111							
Name	0Eh	TEST1 (*1)							
Name	0Fh				TES1	Γ2 (*1)			

SSEL = High

	Address	7	6	5	4	3	2	1	0
Name		PO	WER	IV GA	IV GAIN SEL		SEL	IV GAIN2	
Default	Ι Γ	(00	(00	0	0	1	0
Value	10h		ower on 10: Sleep	*	[*] 4	00/0² 10: I 11:	DVD	*4	
Name				•	BD	GAIN			
Default	11h	1	1	1	1	1	1	1	1
Value					00000000	to 11111111			
Name					DVD	GAIN			
Default	12h	1	1	1	1	1	1	1	1
Value					00000000	to 11111111			
Name					CD	GAIN			
Default	13h	1	1	1	1	1	1	1	1
Value		00000000 to 11111111							
Name	1Eh	TEST1 (*1)							
Name	1Fh		TEST2 (*1)						

Continued on next page.

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SSEL = Open

	Address	7	6	5	4	3	2	1	0
Name		PO	WER	IV GA	IV GAIN SEL		GAIN SEL		
Default	1	(00	(00	C	00	1	0
Value	70h	11: Pc	wer on	,	* 4	00/0	1: BD	*4	
		00/01/1	0: Sleep			10:	DVD		
						11:	CD		
Name					BD (GAIN			
Default	71h	1	1	1	1	1	1	1	1
Value					00000000 t	o 11111111			
Name					DVD	GAIN			
Default	72h	1	1	1	1	1	1	1	1
Value					00000000 t	o 11111111			
Name					CD (GAIN			
Default	73h	1	1	1	1	1	1	1	1
Value		00000000 to 11111111							
Name	7Eh		TEST1 (*1)						
Name	7Fh				TEST	T2 (*1)			

^{*1} TEST1 and TEST2 are either the time when power is applied or "00000000" is set. Do not attempt to change "00000000" during operation. "00000000" is returned when reading is made.

I/V amplifier gain setting table

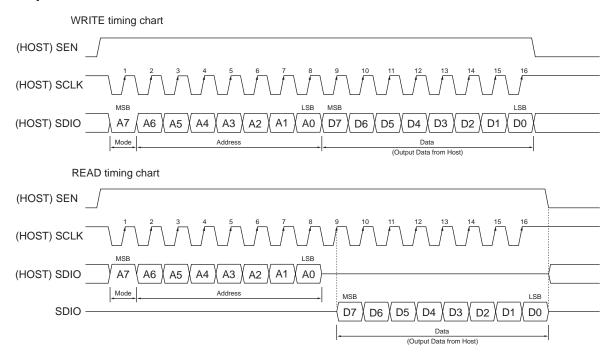
00h/10	h/70h	5	4	1		
Nar	ne	IV GAI	IV GAIN1 SET			
Defa	ault	0	00		00 1	
	High2	00/01		00/01		1
	High1	10/11		1		
IV GAIN	Middle2	00/01		00/01		0
	Middle1	10		10		0
	Low	11		11		0

^{*2} No problem in terms of operation occurs even when writing is made to the address 04h to 0Dh and 14h to 1Dh and 74h to 7Dh. "00000000" is returned when this address is read.

^{*3} When I performed address reading except the register group set by an SSEL terminal, I keep Hi-Z without paying a value.

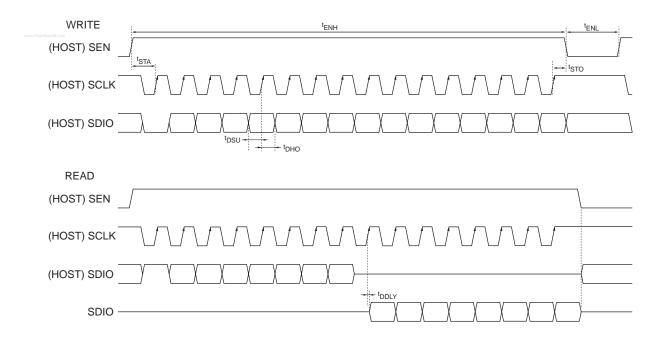
^{*4} Please set the gain setting of the I/V amplifier referring to the table below.

Serial protocol



SDIO pin load / CL=20pF (The table below shows the design reference value.)

Parameter	Symbol	Min.	Тур.	Max.	Unit
SCL clock frequency Write	fSCL	0		10	MHz
SCL clock frequency Read	fSCL	0		4	MHz
SDIO data setup time	t _{DSU}	50			ns
SDIO data hold time	t _{DHO}	50			ns
SDIO output delay	t _{DDLY}		10	80	ns
SEN "H" period	t _{ENH}	1.6			μS
SEN "L" period	t _{ENL}	200			ns
SCL rise time after SEN rise	^t STA	60			ns
SEN fall time after final SCL rise	^t STO	100			ns
Serial input "H" voltage	V _I H	2.4		3.7	V
Serial input "L" voltage	V _I L			0.6	V
SDIO output "H" voltage	V _O H	2.5	2.9	3.3	V
SDIO output "L" voltage	V _O L	0	0.3	0.8	V



Pin	Туре	Equivalent circuit diagram
SDIO	Input Output	3V 3V \$125kΩ 100kΩ
VOP VON	Output	20Ω
SCLK SEN	Input	3V 100kΩ m
SSEL	Input	800kΩ 5kΩ 200kΩ 200kΩ 200kΩ

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